TPH2R408QM & TPN19008QM

Two new 80V N-channel power MOSFETs

Based upon the U-MOSX-H process, the new devices will significantly enhance power supply efficiency



Features

- Lowest Rds(on) in Form factor
- Excellent low FOM Rds(on) x Q(oss) and Rds(on) x Q(sw)
- tj: 175°C

Advantages

- Low conduction loss
- High efficiency switching
- More thermal head room

Benefits

- Lower heat generation
- Smaller space consumption, helping to reduce costs